

FM200TU-3A

HIGH POWER SWITCHING USE
INSULATED PACKAGE

FM200TU-3A



- ID(rms) 100A
- VDSS..... 150V
- Insulated Type
- 6-elements in a pack
- Thermistor inside
- UL Recognized

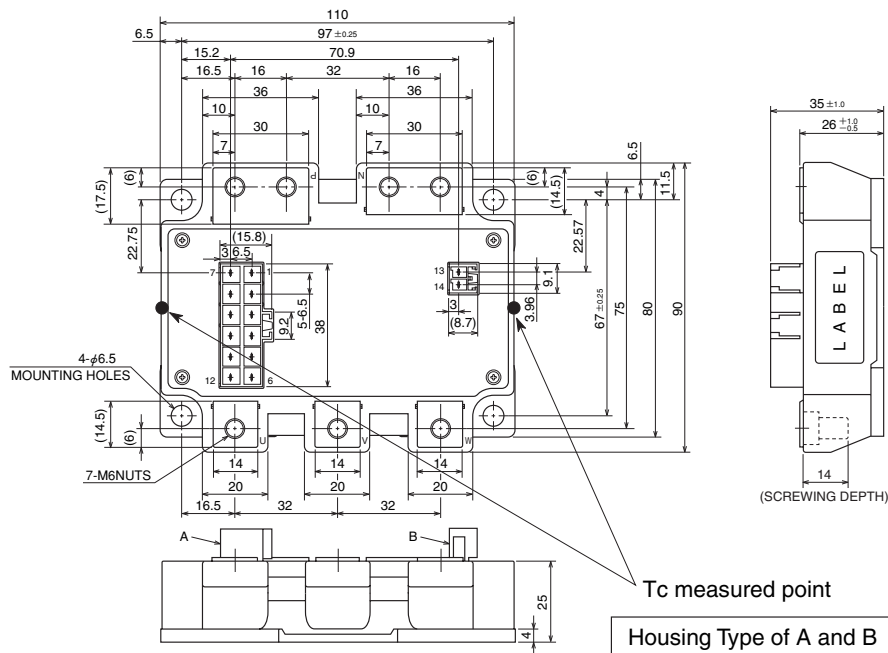
Yellow Card No.E80276
File No.E80271

APPLICATION

AC motor control of forklift (battery power source), UPS

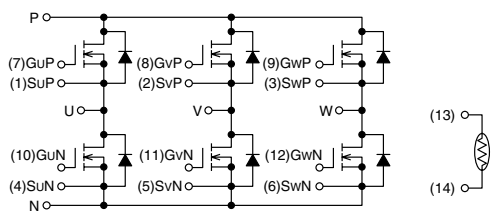
OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Tc measured point
Housing Type of A and B
(Tyco Electronics P/N:)
A: 917353-1
B: 179838-1

CIRCUIT DIAGRAM



(1)SuP	(2)SvP	(3)SwP	(4)SuN	(5)SvN	(6)SwN	A
(7)GuP	(8)GvP	(9)GwP	(10)GuN	(11)GvN	(12)GwN	A
(13)TH1	(14)TH2					B

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HIGH POWER SWITCHING USE
INSULATED PACKAGEABSOLUTE MAXIMUM RATINGS (T_{ch} = 25°C unless otherwise specified.)

Symbol	Item	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	G-S Short	150	V
V _{GSS}	Gate-source voltage	D-S Short	±20	V
I _D	Drain current	T _C ' = 122°C* ³	100	A
I _{DM}		Pulse* ²	200	A
I _{DA}	Avalanche current	L = 10μH Pulse* ²	100	A
I _S * ¹	Source current		100	A
I _{SM} * ¹		Pulse* ²	200	A
P _D * ⁴	Maximum power dissipation	T _C = 25°C	410	W
P _D * ⁴		T _C ' = 25°C* ³	560	W
T _{ch}	Channel temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +125	°C
V _{iso}	Isolation voltage	Main terminal to base plate, AC 1 min.	2500	V
—	Mounting torque	Main Terminal M6	3.5 ~ 4.5	N • m
—		Mounting M6	3.5 ~ 4.5	N • m
—	Weight	Typical value	600	g

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C unless otherwise specified.)

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{DSS}	Drain cutoff current	V _{DS} = V _{DSS} , V _{GS} = 0V	—	—	1	mA	
V _{GS(th)}	Gate-source threshold voltage	I _D = 10mA, V _{DS} = 10V	4.7	6	7.3	V	
I _{GSS}	Gate leakage current	V _{GS} = V _{GSS} , V _{DS} = 0V	—	—	1.5	μA	
r _{DS(ON)}	Static drain-source (chip) On-state resistance	I _D = 100A V _{GS} = 15V	T _{ch} = 25°C	—	4.8	6.6	mΩ
			T _{ch} = 125°C	—	9.1	—	
V _{DS(ON)}	Static drain-source (chip) On-state voltage	I _D = 100A V _{GS} = 15V	T _{ch} = 25°C	—	0.48	0.66	V
			T _{ch} = 125°C	—	0.91	—	
R _(lead)	Lead resistance	I _D = 100A terminal-chip	T _{ch} = 25°C	—	1.2	—	mΩ
			T _{ch} = 125°C	—	1.68	—	
C _{iss}	Input capacitance	V _{DS} = 10V V _{GS} = 0V	—	—	50	nF	
C _{oss}	Output capacitance		—	—	7		
C _{rss}	Reverse transfer capacitance		—	—	4		
Q _G	Total gate charge	V _{DD} = 80V, I _D = 100A, V _{GS} = 15V	—	820	—	nC	
t _{d(on)}	Turn-on delay time	V _{DD} = 80V, I _D = 100A, V _{GS1} = V _{GS2} = 15V R _G = 13Ω, Inductive load switching operation I _S = 100A	—	—	400	ns	
t _r	Turn-on rise time		—	—	250		
t _{d(off)}	Turn-off delay time		—	—	450		
t _f	Turn-off fall time		—	—	200		
t _{rr} * ¹	Reverse recovery time		—	—	200		
Q _{rr} * ¹	Reverse recovery charge		—	6.5	—		μC
V _{SD} * ¹	Source-drain voltage		I _S = 100A, V _{GS} = 0V	—	—		1.3
R _{th(ch-c)}	Thermal resistance	MOSFET part (1/6 module)* ⁷	—	—	0.30	°C/W	
R _{th(ch-c')}		MOSFET part (1/6 module)* ³	—	—	0.22		
R _{th(c-f)}	Contact thermal resistance	Case to fin, Thermal grease Applied* ⁸ (1/6 module)	—	0.1	—		
R _{th(c'-f)}		Case to fin, Thermal grease Applied* ^{3, 8} (1/6 module)	—	0.09	—		

THERMISTOR PART

Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R _{TH} * ⁶	Resistance	T _{TH} = 25°C* ⁵	—	100	—	kΩ
B* ⁶	B Constant	Resistance at T _{TH} = 25°C, 50°C* ⁵	—	4000	—	K

*1: It is characteristics of the anti-parallel, source to drain free-wheel diode (FWDi).

*2: Pulse width and repetition rate should be such that the device channel temperature (T_{ch}) does not exceed T_{ch} max rating.*3: T_C' measured point is just under the chips. If use this value, R_{th(f-a)} should be measured just under the chips.

*4: Pulse width and repetition rate should be such as to cause negligible temperature rise.

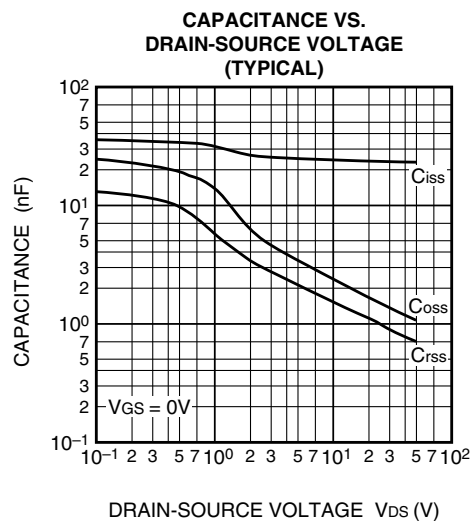
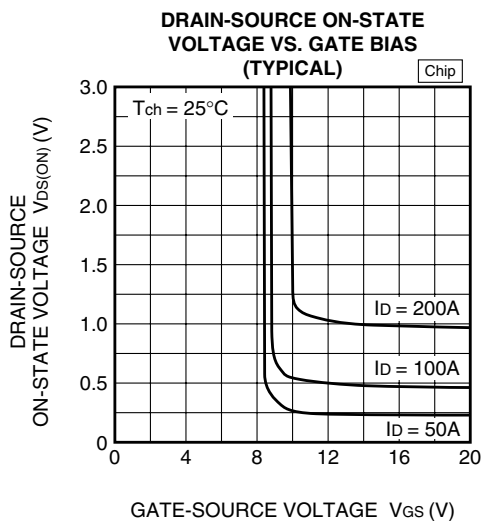
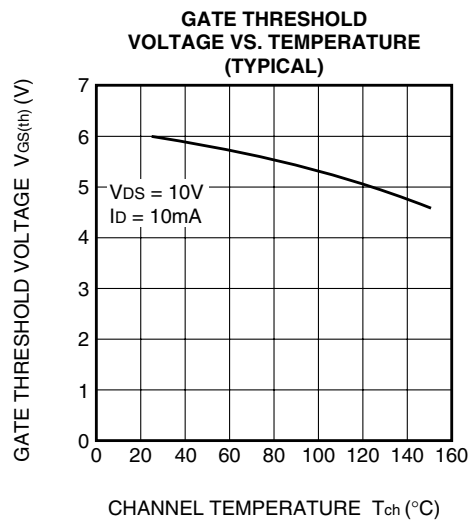
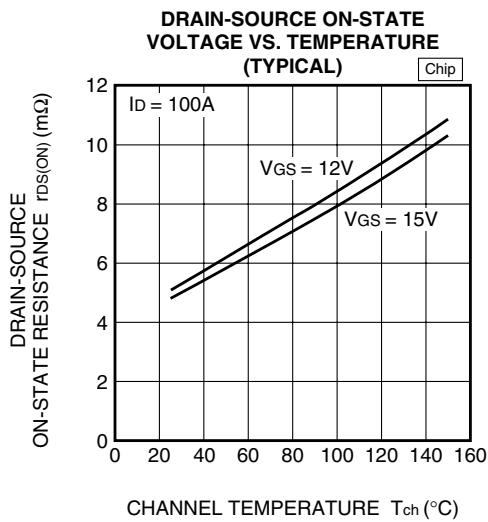
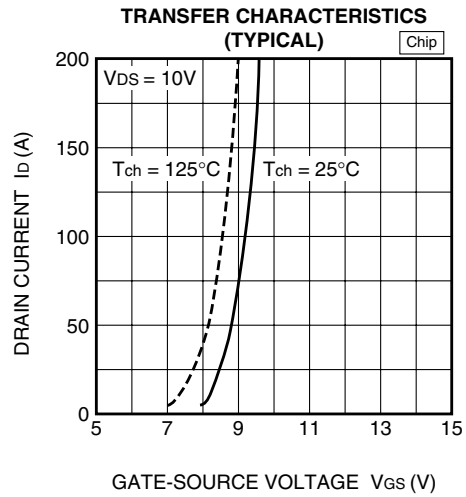
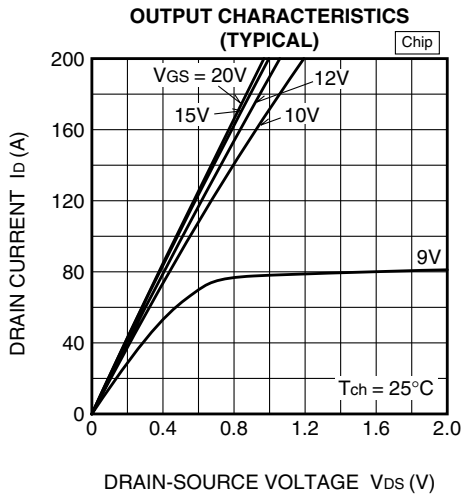
*5: T_{TH} is thermistor temperature.*6: B = (lnR₁ - lnR₂) / (1/T₁ - 1/T₂) R₁: Resistance at T₁(K), R₂: Resistance at T₂(K)*7: T_C measured point is shown in page OUTLINE DRAWING.

*8: Typical value is measured by using Shin-Etsu Chemical Co., Ltd "G-746".

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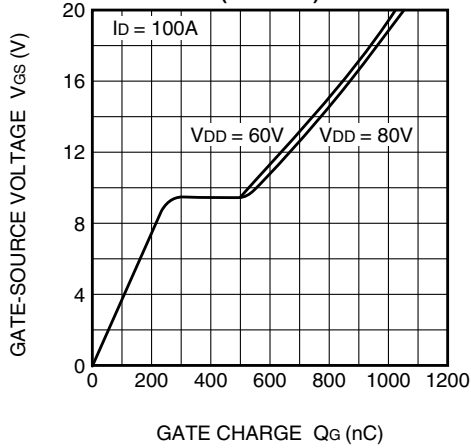
PERFORMANCE CURVES



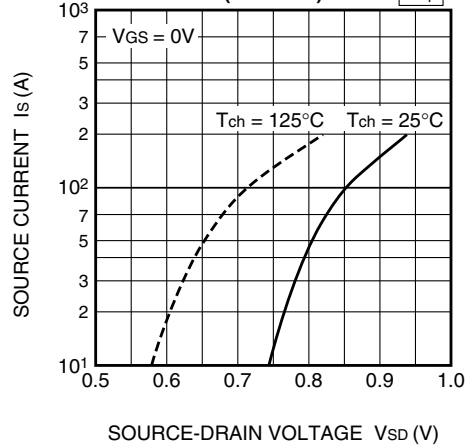
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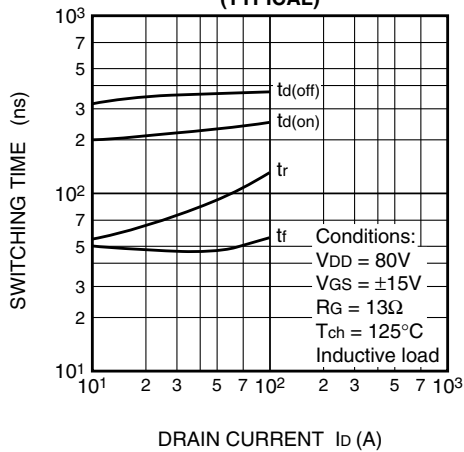
GATE CHARGE CHARACTERISTICS (TYPICAL)



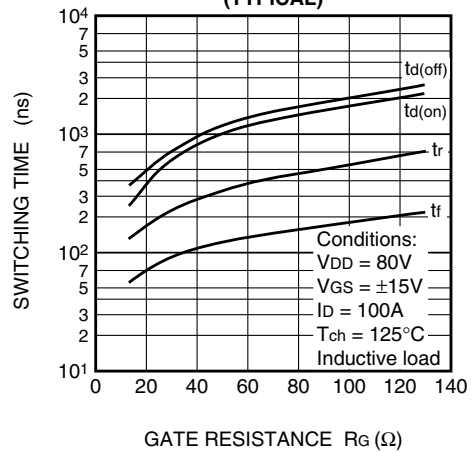
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



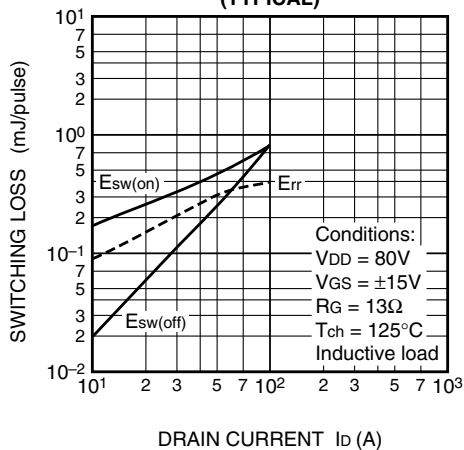
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



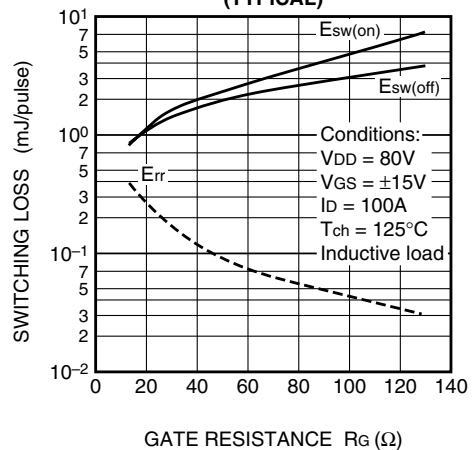
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



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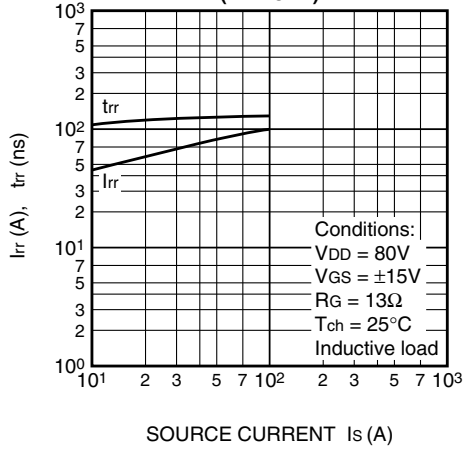
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



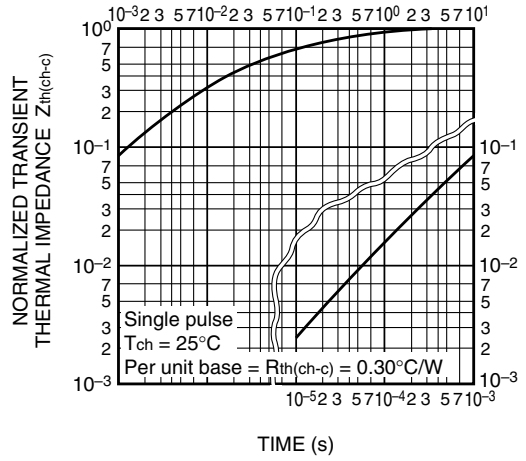
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REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE
(TYPICAL)



TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS



CHIP LAYOUT

